

Document Title**32M x 8 Bit SmartMedia™ Card**Revision History

Revision No	History	Draft Date	Remark																					
0.0	Initial issue(16MB Dual Chip) - Compared to SMFV032(32MB Single Chip) 1. Valid block number(Min.) SMFDV032 : 2013 blocks SMFV032 : 2018 blocks 2. Input/output capacitance & input capacitance(Max.) SMFDV032 : 30 pF SMFV032 : 70 pF	Nov 11th 1998	Preliminary																					
0.1	Changed specifications from 16MB to 32MB	Jan 14th 1999	Final																					
	<table><tr><th>ITEM</th><th>SMFV016</th><th>SMFDV032</th></tr><tr><td>Valid Block Number(Min.)</td><td>1004 Blocks</td><td>2013 Blocks</td></tr><tr><td>Sequential Read Mode</td><td>OK</td><td>Supported only within a block</td></tr><tr><td>Input/output & input Capacitance</td><td>10pF</td><td>30pF</td></tr><tr><td>Device Code</td><td>73H</td><td>75H</td></tr><tr><td>Program Icc2(mA)</td><td>Typ : 10, Max : 20</td><td>Typ : 15, Max : 25</td></tr><tr><td>Erase Icc3(mA)</td><td>Typ : 10, Max : 20</td><td>Typ : 15, Max : 25</td></tr></table>	ITEM	SMFV016	SMFDV032	Valid Block Number(Min.)	1004 Blocks	2013 Blocks	Sequential Read Mode	OK	Supported only within a block	Input/output & input Capacitance	10pF	30pF	Device Code	73H	75H	Program Icc2(mA)	Typ : 10, Max : 20	Typ : 15, Max : 25	Erase Icc3(mA)	Typ : 10, Max : 20	Typ : 15, Max : 25		
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0.2	Data Sheet 1999 1. Changed t_R Parameter : 7μs(Max.) → 10μs(Max.) 2. Changed Nop : Main Array 1 cycle(Max.) → 2 cycles(Max.) 3. Added \overline{CE} don't care mode during the data-loading and reading	April 10th 1999	Final																					
0.3	1. Changed voltage-density model marking method on SmartMedia	June 7th 1999	Final																					
0.4	1. Revised real-time map-out algorithm(refer to technical notes)	June 30th 1999	Final																					
0.5	1. Changed device name - SMFDV032 -> K9D5608V0M-SSB0	Sep.15th 1999	Final																					
0.6	1. Changed invalid block(s) marking method prior to shipping - Physical format standard specifies that block status is defined by the 6th byte in the spare area. Samsung makes sure that the first page of every invalid block has 00h data at the column address of 517(4MB SmartMedia and higher densities) or 261(2MB SmartMedia). --> Physical format standard by SSFDC Forum specifies that for the invalid blocks the 6th byte in the spare area (column address 517 for 4MB SmartMedia and higher densities, 261 for 2MB SmartMedia, respectively) contains two or more "0" bits to indicate a invalid block.	July 17th 2000	Final																					

Note : For more detailed features and specifications including FAQ, please refer to Samsung's Flash web site.
<http://www.intl.samsungsemi.com/Memory/Flash/datasheets.html>

The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions about device. If you have any questions, please contact the SAMSUNG branch office near your office.

32M x 8 Bit SmartMedia™ Card

FEATURES

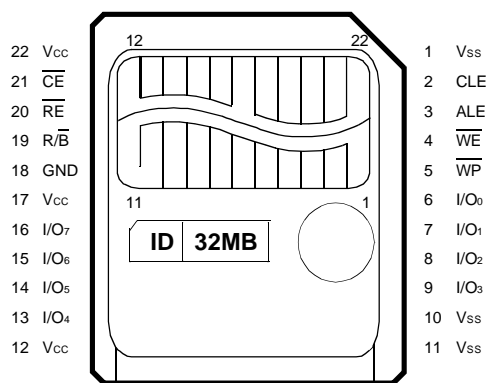
- Single 2.7V~3.6V Supply
- Organization
 - Memory Cell Array : (32M + 1,024K)bit x 8bit
 - Data Register : (512 + 16)bit x 8bit
- Automatic Program and Erase
 - Page Program : (512 + 16)Byte
 - Block Erase : (16K + 512)Byte
- 528-Byte Page Read Operation
 - Random Access : 10μs(Max.)
 - Serial Page Access : 50ns(Min.)
- Fast Write Cycle Time
 - Program Time : 200μs(typ.)
 - Block Erase Time : 2ms(typ.)
- Command/Address/Data Multiplexed I/O port
- Hardware Data Protection
 - Program/Erase Lockout During Power Transitions
- Reliable CMOS Floating-Gate Technology
 - Endurance : 1Million Program/Erase Cycles
 - Data Retention : 10 years
- Command Register Operation
- 22pad SmartMedia™(SSFDC)
- ID for Copyright Protection

GENERAL DESCRIPTION

The K9D5608V0M is a 32M(33,554,432)x8bit NAND Flash Memory with a spare 1,024K(1,048,576)x8bit. Its NAND cell provides the most cost-effective solution for the solid state mass storage market. A program operation programs the 528-byte page in typically 200μs and an erase operation can be performed in typically 2ms on a 16K-byte block. Data in the page can be read out at 50ns cycle time per byte. The I/O pins serve as the ports for address and data input/output as well as command inputs. The on-chip write controller automates all program and erase functions including pulse repetition, where required, and internal verify and margining of data. Even the write-intensive systems can take advantage of the K9D5608V0M's extended reliability of 1,000,000 program/erase cycles by providing ECC(Error Correcting Code) with real time mapping-out algorithm.

The K9D5608V0M is an optimum solution for large nonvolatile storage applications such as solid state file storage, digital voice recorder, digital still camera and other portable applications requiring non-volatility.

SmartMedia™ CARD(SSFDC)



22 PAD SmartMedia™

PIN DESCRIPTION

Pin Name	Pin Function
I/O0 ~ I/O7	Data Input/Outputs
CLE	Command Latch Enable
ALE	Address Latch Enable
$\overline{\text{CE}}$	Chip Enable
$\overline{\text{RE}}$	Read Enable
$\overline{\text{WE}}$	Write Enable
$\overline{\text{WP}}$	Write Protect
GND	Ground
R/ $\overline{\text{B}}$	Ready/Busy output
Vcc	Power
Vss	Ground
N.C	No Connection

NOTE : Connect all Vcc and Vss pins of each device to common power supply outputs.
Do not leave Vcc or Vss disconnected.

Figure 1. FUNCTIONAL BLOCK DIAGRAM

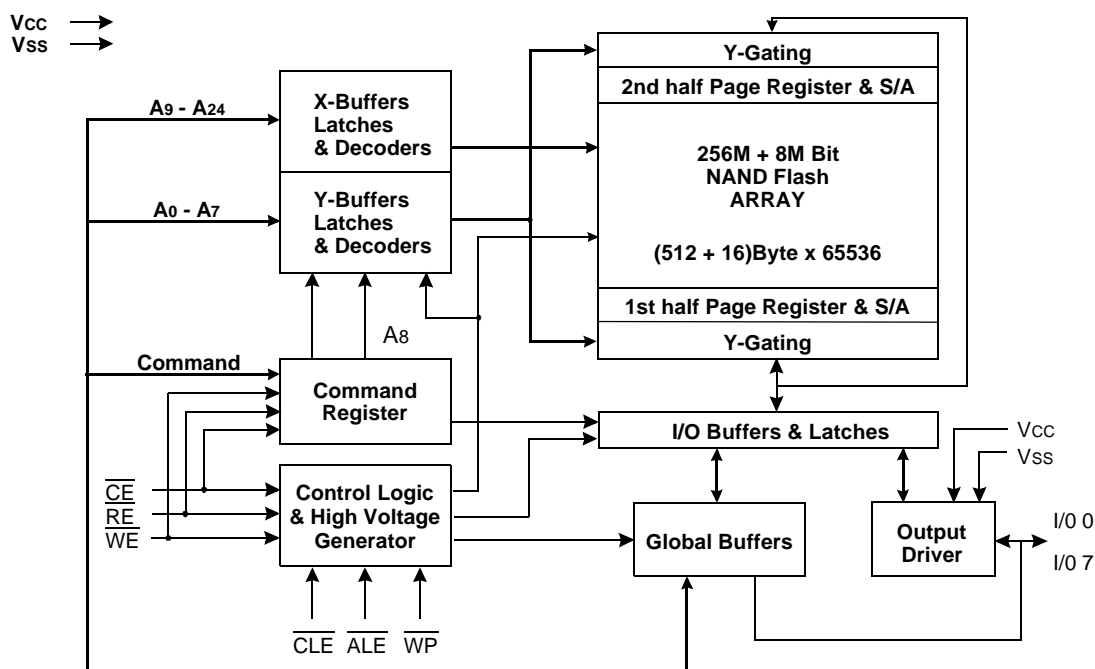
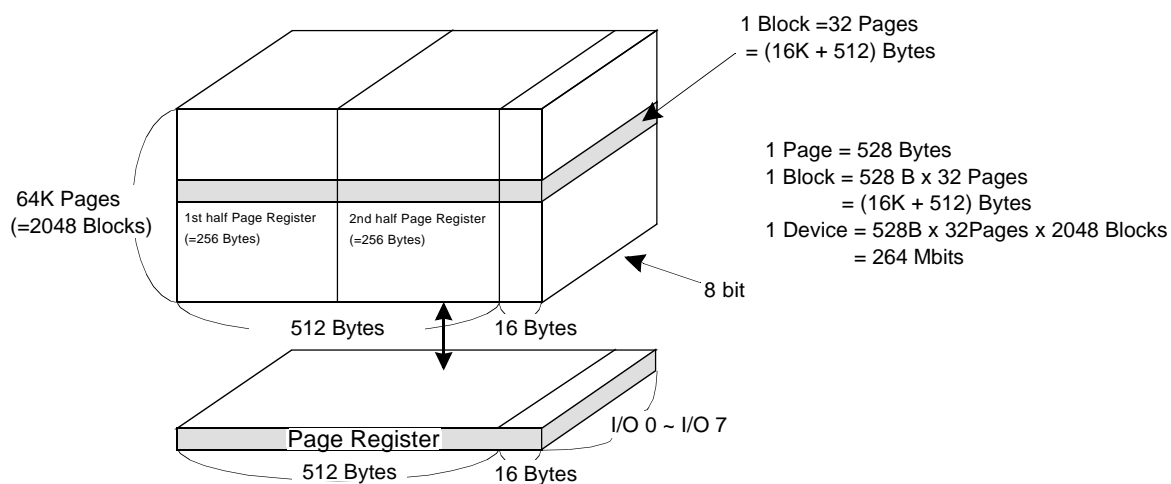


Figure 2. ARRAY ORGANIZATION



	I/O 0	I/O 1	I/O 2	I/O 3	I/O 4	I/O 5	I/O 6	I/O 7	
1st Cycle	A0	A1	A2	A3	A4	A5	A6	A7	Column Address
2nd Cycle	A9	A10	A11	A12	A13	A14	A15	A16	Row Address (Page Address)
3rd Cycle	A17	A18	A19	A20	A21	A22	A23	A24	

NOTE : Column Address : Starting Address of the Register.

00h Command(Read) : Defines the starting address of the 1st half of the register.

01h Command(Read) : Defines the starting address of the 2nd half of the register.

* A₈ is set to "Low" or "High" by the 00h or 01h Command.

PRODUCT INTRODUCTION

The K9D5608V0M is a 264Mbit(276,824,064 bit) memory organized as 65,536 rows(pages) by 528 columns. Spare sixteen columns are located from column address of 512 to 527. A 528-byte data register is connected to memory cell arrays accommodating data transfer between the I/O buffers and memory during page read and page program operations. The memory array is made up of 16 cells that are serially connected to form a NAND structure. Each of the 16 cells resides in a different page. A block consists of the 32 pages formed by two NAND structures, totaling 8448 NAND structures of 16 cells. The array organization is shown in Figure 2. The program and read operations are executed on a page basis, while the erase operation is executed on a block basis. The memory array consists of 2048 separately erasable 16K-byte blocks. It indicates that the bit by bit erase operation is prohibited on the K9D5608V0M.

The K9D5608V0M has addresses multiplexed into 8 I/O's. This scheme dramatically reduces pin counts and allows systems upgrades to future densities by maintaining consistency in system board design. Command, address and data are all written through I/O's by bringing \overline{WE} to low while \overline{CE} is low. Data is latched on the rising edge of \overline{WE} . Command Latch Enable(CLE) and Address Latch Enable(ALE) are used to multiplex command and address respectively, via the I/O pins. All commands require one bus cycle except for Block Erase command which requires two cycles: one cycle for erase-setup and another for erase-execution after block address loading. The 32M byte physical space requires 25 addresses, thereby requiring three cycles for byte-level addressing: column address, low row address and high row address, in that order. Page Read and Page Program need the same three address cycles following the required command input. In Block Erase operation, however, only the two row address cycles are used. Device operations are selected by writing specific commands into the command register. Table 1 defines the specific commands of the K9D5608V0M.

Table 1. COMMAND SETS

Function	1st. Cycle	2nd. Cycle	Acceptable Command during Busy
Read 1	00h/01h ⁽¹⁾	-	
Read 2	50h	-	
Read ID	90h	-	
Reset	FFh	-	O
Page Program	80h	10h	
Block Erase	60h	D0h	
Read Status	70h	-	O

NOTE : 1. The 00h command defines starting address of the 1st half of registers.

The 01h command defines starting address of the 2nd half of registers.

After data access on the 2nd half of register by the 01h command, the status pointer is automatically moved to the 1st half register(00h) on the next cycle.

PIN DESCRIPTION**Command Latch Enable(CLE)**

The CLE input controls the path activation for commands sent to the command register. When active high, commands are latched into the command register through the I/O ports on the rising edge of the WE signal.

Address Latch Enable(ALE)

The ALE input controls the activating path for address to the internal address registers. Addresses are latched on the rising edge of WE with ALE high.

Chip Enable(CE)

The CE input is the device selection control. When CE goes high during a read operation the device is returned to standby mode. However, when the device is in the busy state during program or erase, CE high is ignored, and does not return the device to standby mode.

Write Enable(WE)

The WE input controls writes to the I/O port. Commands, address and data are latched on the rising edge of the WE pulse.

Read Enable(RE)

The RE input is the serial data-out control, and when active drives the data onto the I/O bus. Data is valid t_{REA} after the falling edge of RE which also increments the internal column address counter by one.

I/O Port : I/O 0 ~ I/O 7

The I/O pins are used to input command, address and data, and to output data during read operations. The I/O pins float to high-z when the chip is deselected or when the outputs are disabled.

Write Protect(WP)

The WP pin provides inadvertent write/erase protection during power transitions. The internal high voltage generator is reset when the WP pin is active low.

Ready/Busy(R/B)

The R/B output indicates the status of the device operation. When low, it indicates that a program, erase or random read operation is in process and returns to high state upon completion. It is an open drain output and does not float to high-z condition when the chip is deselected or when outputs are disabled.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Voltage on any pin relative to Vss	V _{IN}	-0.6 to + 4.6	V
	V _{CC}	-0.6 to + 4.6	
Temperature Under Bias	T _{BIAS}	-10 to +65	°C
Storage Temperature	T _{STG}	-20 to +65	°C

NOTE :

- Minimum DC voltage is -0.3V on input/output pins. During transitions, this level may undershoot to -2.0V for periods <30ns.
Maximum DC voltage on input/output pins is V_{CC}+0.3V which, during transitions, may overshoot to V_{CC}+2.0V for periods <20ns.
- Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING CONDITIONS

(Voltage reference to GND, T_A=0 to 55°C)

Parameter	Symbol	Min	Typ.	Max	Unit
Supply Voltage	V _{CC}	2.7	3.3	3.6	V
Supply Voltage	V _{SS}	0	0	0	V

DC AND OPERATING CHARACTERISTICS(Recommended operating conditions otherwise noted.)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Operating Current	Sequential Read	I _{CC1}	t _{RC} =50ns, $\overline{CE}=V_{IL}$, I _{OUT} =0mA	-	10	20	mA
	Program	I _{CC2}	-	-	15	25	
	Erase	I _{CC3}	-	-	15	25	
Stand-by Current(TTL)		I _{SB1}	$\overline{CE}=V_{IH}$, $\overline{WP}=0V/V_{CC}$	-	-	1	μA
Stand-by Current(CMOS)		I _{SB2}	$\overline{CE}=V_{CC}-0.2$, $\overline{WP}=0V/V_{CC}$	-	10	50	
Input Leakage Current		I _{LI}	V _{IN} =0 to 3.6V	-	-	±10	
Output Leakage Current		I _{LO}	V _{OUT} =0 to 3.6V	-	-	±10	
Input High Voltage, All inputs		V _{IH}	-	2.0	-	V _{CC} +0.3	V
Input Low Voltage, All inputs		V _{IL}	-	-0.3	-	0.8	
Output High Voltage Level		V _{OH}	I _{OH} =-400μA	2.4	-	-	
Output Low Voltage Level		V _{OL}	I _{OL} =2.1mA	-	-	0.4	
Output Low Current(R/B)		I _{OL} (R/B)	V _{OL} =0.4V	8	10	-	mA

VALID BLOCK

Parameter	Symbol	Min	Typ.	Max	Unit
Valid Block Number	NvB	2013	-	2048	Blocks

NOTE :

1. The K9D5608V0M may include invalid blocks when first shipped. Additional invalid blocks may develop while being used. The number of valid blocks is presented with both cases of invalid blocks considered. Invalid blocks are defined as blocks that contain one or more bad bits. **Do not try to access these invalid blocks for program and erase.** Refer to the attached technical notes for a appropriate management of invalid blocks.
2. Per the specification of the physical format version 1.2 by SSFDC forum, minimum 1,000 valid blocks are guaranteed for each 16MB memory space

AC TEST CONDITION

(TA=0 to 55°C, VCC=2.7V~3.6V unless otherwise noted)

Parameter	Value
Input Pulse Levels	0.4V to 2.4V
Input Rise and Fall Times	5ns
Input and Output Timing Levels	1.5V
Output Load (3.0V +/-10%)	1 TTL GATE and CL=50pF
Output Load (3.3V +/-10%)	1 TTL GATE and CL=100pF

CAPACITANCE(TA=25°C, VCC=3.3V, f=1.0MHz)

Item	Symbol	Test Condition	Min	Max	Unit
Input/Output Capacitance	C _{I/O}	V _{IL} =0V	-	30	pF
Input Capacitance	C _{IN}	V _{IN} =0V	-	30	pF

NOTE : Capacitance is periodically sampled and not 100% tested.

MODE SELECTION

CLE	ALE	CE	WE	RE	WP	Mode	
H	L	L		H	X	Read Mode	Command Input
L	H	L		H	X		Address Input(3clock)
H	L	L		H	H	Write Mode	Command Input
L	H	L		H	H		Address Input(3clock)
L	L	L		H	H	Data Input	
L	L	L	H		X	sequential Read & Data Output	
L	L	L	H	H	X	During Read(Busy)	
X	X	X	X	X	H	During Program(Busy)	
X	X	X	X	X	H	During Erase(Busy)	
X	X ⁽¹⁾	X	X	X	L	Write Protect	
X	X	H	X	X	0V/VCC ⁽²⁾	Stand-by	

NOTE : 1. X can be V_{IL} or V_{IH}.

2. WP should be biased to CMOS high or CMOS low for standby.

Program/Erase Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Program Time	t _{PROG}	-	200	500	μs
Number of Partial Program Cycles in the Same Page	Main Array	-	-	2	cycles
	Spare Array	-	-	3	cycles
Block Erase Time	t _{BERS}	-	2	3	ms

AC Timing Characteristics for Command / Address / Data Input

Parameter	Symbol	Min	Max	Unit
CLE setup Time	tCLS	0	-	ns
CLE Hold Time	tCLH	10	-	ns
$\overline{\text{CE}}$ setup Time	tCS	0	-	ns
$\overline{\text{CE}}$ Hold Time	tCH	10	-	ns
$\overline{\text{WE}}$ Pulse Width	tWP	25	-	ns
ALE setup Time	tALS	0	-	ns
ALE Hold Time	tALH	10	-	ns
Data setup Time	tDS	20	-	ns
Data Hold Time	tDH	10	-	ns
Write Cycle Time	tWC	50	-	ns
$\overline{\text{WE}}$ High Hold Time	tWH	15	-	ns

AC Characteristics for Operation

Parameter	Symbol	Min	Max	Unit
Data Transfer from Cell to Register	tR	-	10	μs
ALE to $\overline{\text{RE}}$ Delay(ID read)	tAR1	100	-	ns
ALE to $\overline{\text{RE}}$ Delay(Read cycle)	tAR2	50	-	ns
$\overline{\text{CE}}$ to $\overline{\text{RE}}$ Delay(ID read)	tCR	100	-	ns
Ready to $\overline{\text{RE}}$ Low	tRR	20	-	ns
$\overline{\text{RE}}$ Pulse Width	tRP	30	-	ns
$\overline{\text{WE}}$ High to Busy	tWB	-	100	ns
Read Cycle Time	tRC	50	-	ns
$\overline{\text{RE}}$ Access Time	tREA	-	35	ns
$\overline{\text{RE}}$ High to Output Hi-Z	tRHZ	15	30	ns
$\overline{\text{CE}}$ High to Output Hi-Z	tCHZ	-	20	ns
$\overline{\text{RE}}$ High Hold Time	tREH	15	-	ns
Output Hi-Z to $\overline{\text{RE}}$ Low	tIR	0	-	ns
Last RE High to Busy(at sequential read)	tRB	-	100	ns
$\overline{\text{CE}}$ High to Ready(in case of interception by $\overline{\text{CE}}$ at read)	tCRY	-	$50 + t_r(R/\overline{B})^{(1)}$	ns
$\overline{\text{CE}}$ High Hold Time(at the last serial read) ⁽²⁾	tCEH	100	-	ns
$\overline{\text{RE}}$ Low to Status Output	tRSTO	-	35	ns
$\overline{\text{CE}}$ Low to Status Output	tCSTO	-	45	ns
$\overline{\text{WE}}$ High to $\overline{\text{RE}}$ Low	tWHR	60	-	ns
$\overline{\text{RE}}$ access time(Read ID)	tREADID	-	35	ns
Device Resetting Time(Read/Program/Erase)	tRST	-	5/10/500	μs

NOTE :

1. The time to Ready depends on the value of the pull-up resistor tied R/ \overline{B} pin.2. To break the sequential read cycle, $\overline{\text{CE}}$ must be held high for longer time than tCEH.

SmartMedia Technical Notes

Invalid Block(s)

Invalid blocks are defined as blocks that contain one or more invalid bits whose reliability is not guaranteed by Samsung. The information regarding the invalid block(s) is so called as the invalid block information. An invalid block(s) does not affect the performance of valid block(s) because it is isolated from the bit line and the common source line by a select transistor. The system design must be able to mask out the invalid block(s) via address mapping.

Identifying Invalid Block(s)

SSFDC Forum specifies the logical format and physical format to ensure compatibility of SmartMedia. Samsung pre-formats SmartMedia in the Forum-compliant format prior to shipping. **Physical format standard by SSFDC Forum specifies that for the invalid blocks the 6th byte in the spare area (column address 517 for 4MB SmartMedia and higher densities, 261 for 2MB SmartMedia, respectively) contains two or more "0" bits to indicate a invalid block. Other than the blocks with format data and the invalid blocks are erased(FFh). Since the invalid block information is also erasable in most cases, it is impossible to recover the information once it has been erased. Therefore, the system must be able to recognize the invalid block(s) based on the original invalid block information and create the invalid block table via the following suggested flow chart(Figure 1). Any intentional erasure of the original invalid block information is prohibited.**

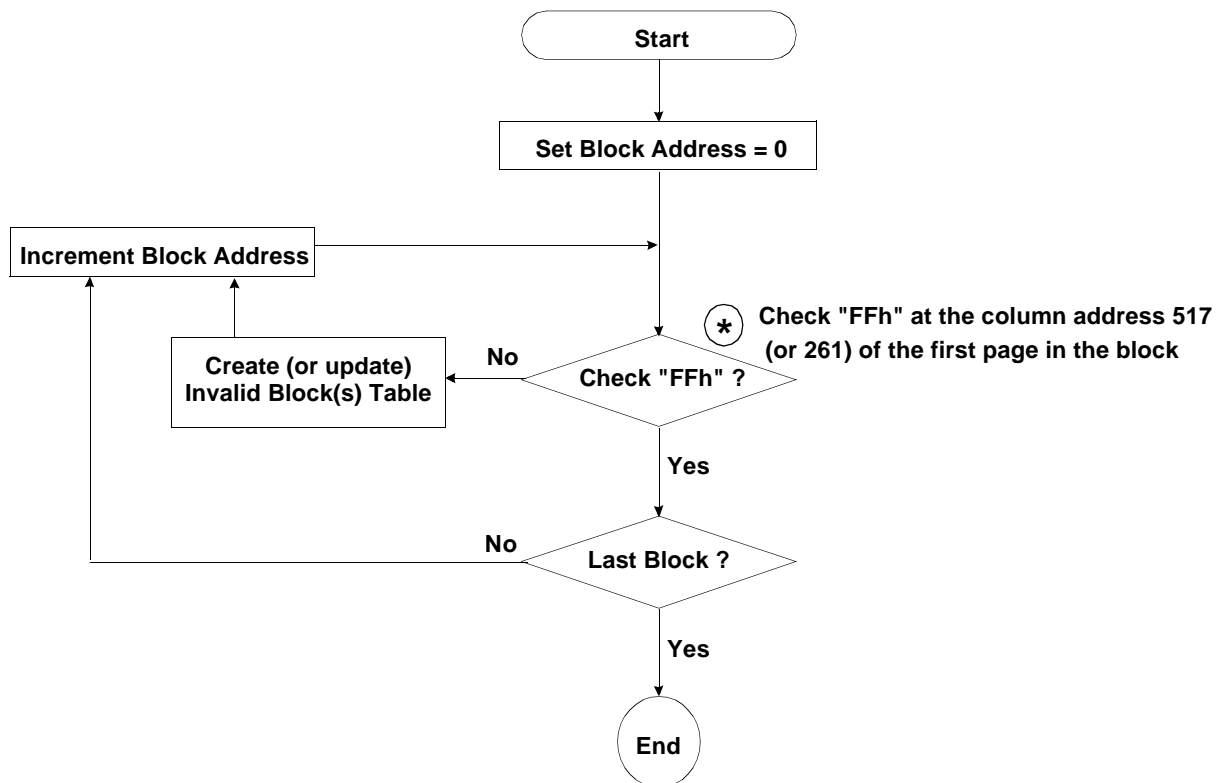


Figure 1. Flow chart to create invalid block table.

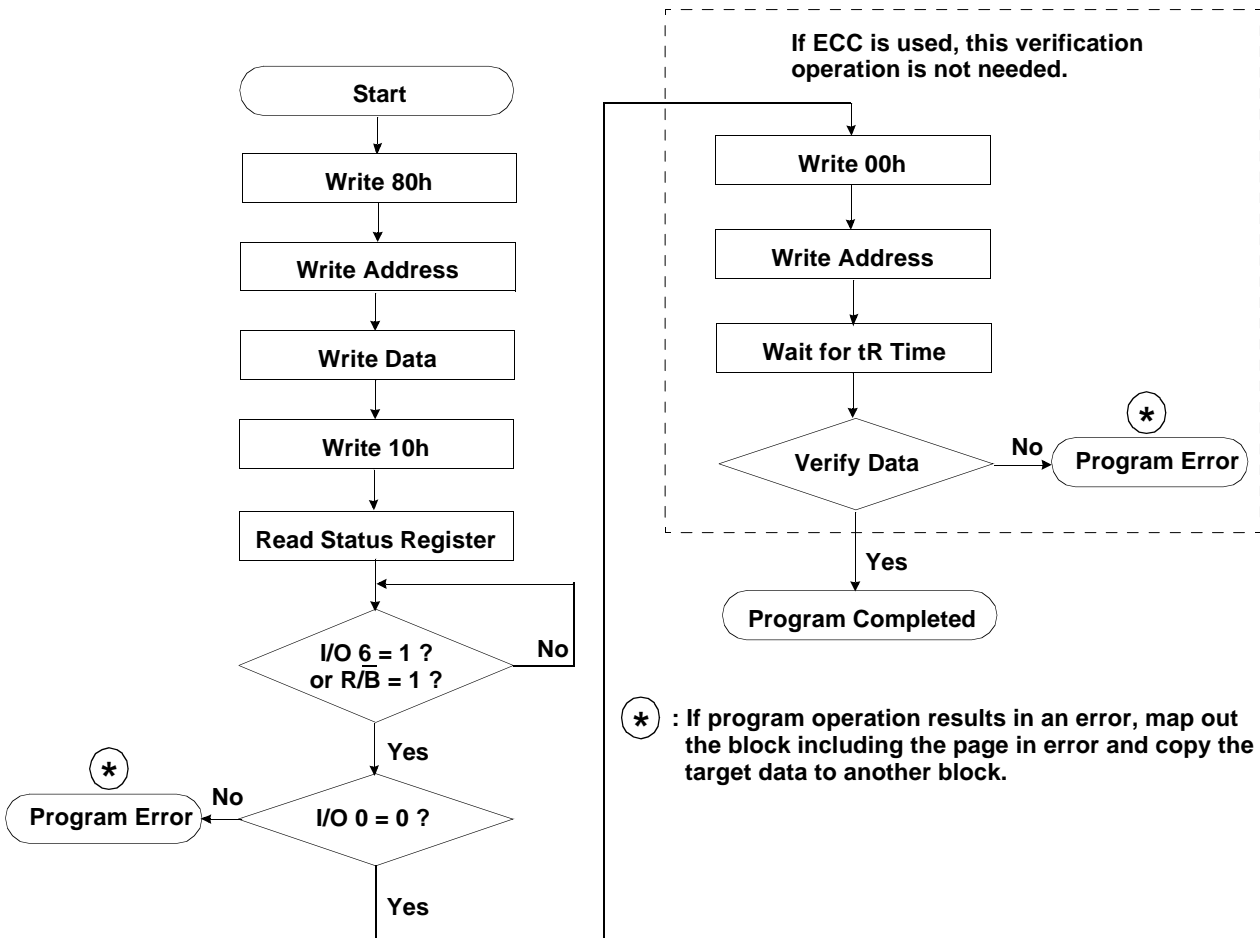
SmartMedia Technical Notes (Continued)**Error in write or read operation**

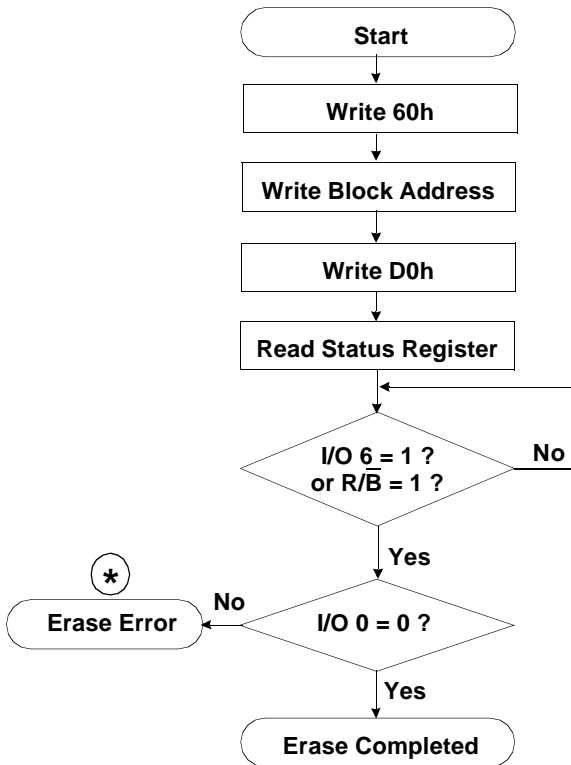
Over its life time, the additional invalid blocks may develop with NAND Flash memory. Refer to the qualification report for the actual data. The following possible failure modes should be considered to implement a highly reliable system. In the case of status read failure after erase or program, block replacement should be done. To improve the efficiency of memory space, it is recommended that the read or verification failure due to single bit error be reclaimed by ECC without any block replacement. The said additional block failure rate does not include those reclaimed blocks.

Failure Mode		Detection and Countermeasure sequence
Write	Erase Failure	Status Read after Erase --> Block Replacement
	Program Failure	Status Read after Program --> Block Replacement Read back (Verify after Program) --> Block Replacement or ECC Correction
Read	Single Bit Failure	Verify ECC -> ECC Correction

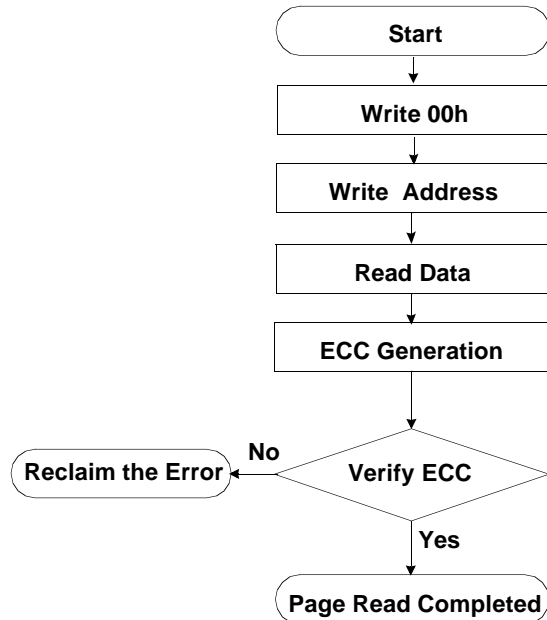
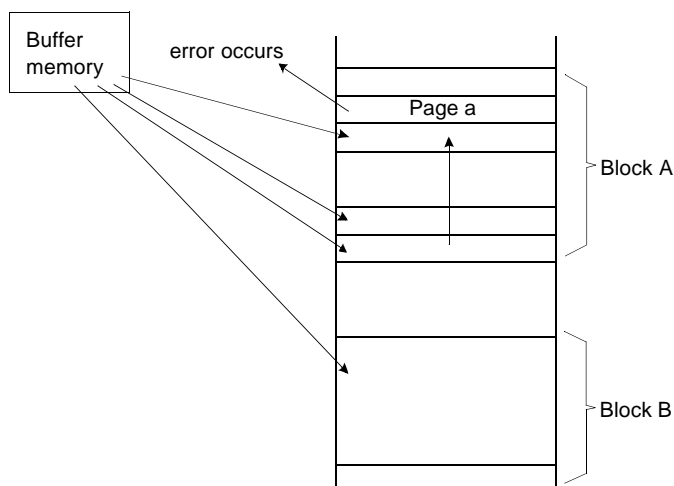
ECC

: Error Correcting Code --> Hamming Code etc.
Example) 1bit correction & 2bit detection

Program Flow Chart

SmartMedia Technical Notes (Continued)**Erase Flow Chart**

(*) : If erase operation results in an error, map out the failing block and replace it with another block.

Read Flow Chart**Block Replacement**

When the error happens with page "a" of Block "A", try to write the data into another Block "B" from an external buffer. Then, prevent further system access to Block "A" (by creating a "invalid block" table or other appropriate scheme.)

Pointer Operation of K9D5608V0M

The K9D5608V0M has three modes to set the destination of the pointer. The pointer is set to "A" area by the "00h" command, to "B" area by the "01h" command, and to "C" area by the "50h" command. Table 1 shows the destination of the pointer, and figure 2 shows the block diagram of its operations.

Table 1. Destination of the pointer

Command	Pointer position	Area
00h	0 ~ 255 byte	1st half array(A)
01h	256 ~ 511 byte	2nd half array(B)
50h	512 ~ 527 byte	spare array(C)

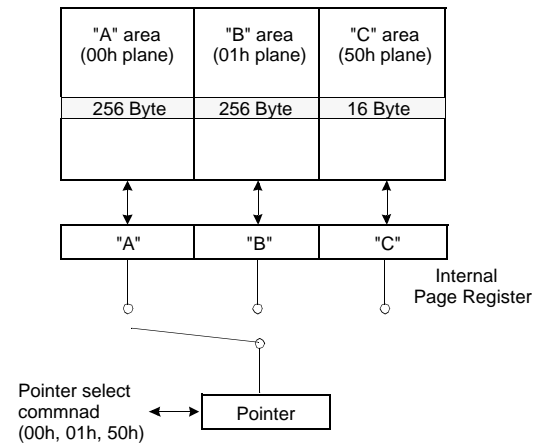
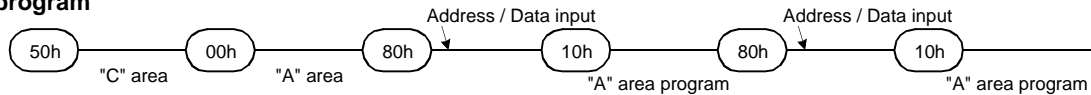


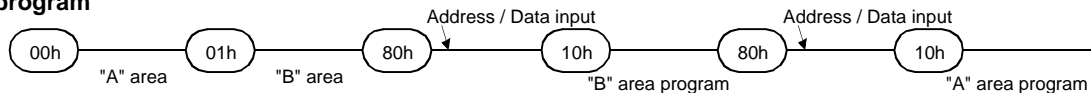
Figure 2. Block Diagram of Pointer Operation

Example of Pointer Operation with Successive Pointer Operation

(1) "A" area program



(2) "B" area program



(3) "C" area program

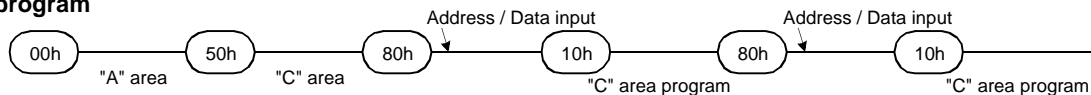


Table 2. Pointer Status after each operation

Operation	Pointer status after operation
Program	With previous 00h, Device is set to 00h Plane With previous 01h, Device is set to 00h Plane* With previous 50h, Device is set to 50h Plane
Reset	"00h" Plane("A" area)
Power up	"00h" Plane("A" area)

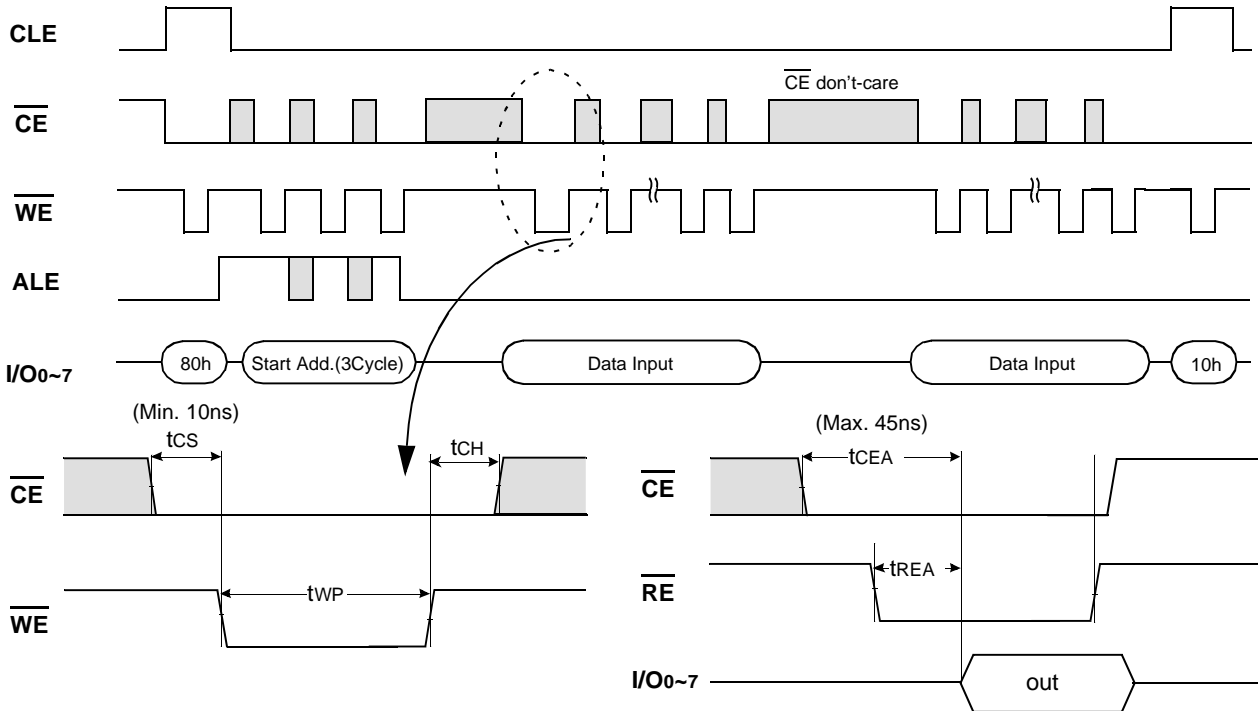
* 01h command is valid just one time when it is used as a pointer for program/erase.

* Erase operation does not affect the pointer status. Previous pointer status is maintained.

System Interface Using $\overline{\text{CE}}$ don't-care.

For a easier system interface, $\overline{\text{CE}}$ may be inactive during the data-loading or sequential data-reading as shown below. The internal 528byte page registers are utilized as seperate buffers for this operation and the system design gets more flexible. In addition, for voice or audio applications which use slow cycle time on the order of u-seconds, de-activating $\overline{\text{CE}}$ during the data-loading and reading would provide significant savings in power consumption.

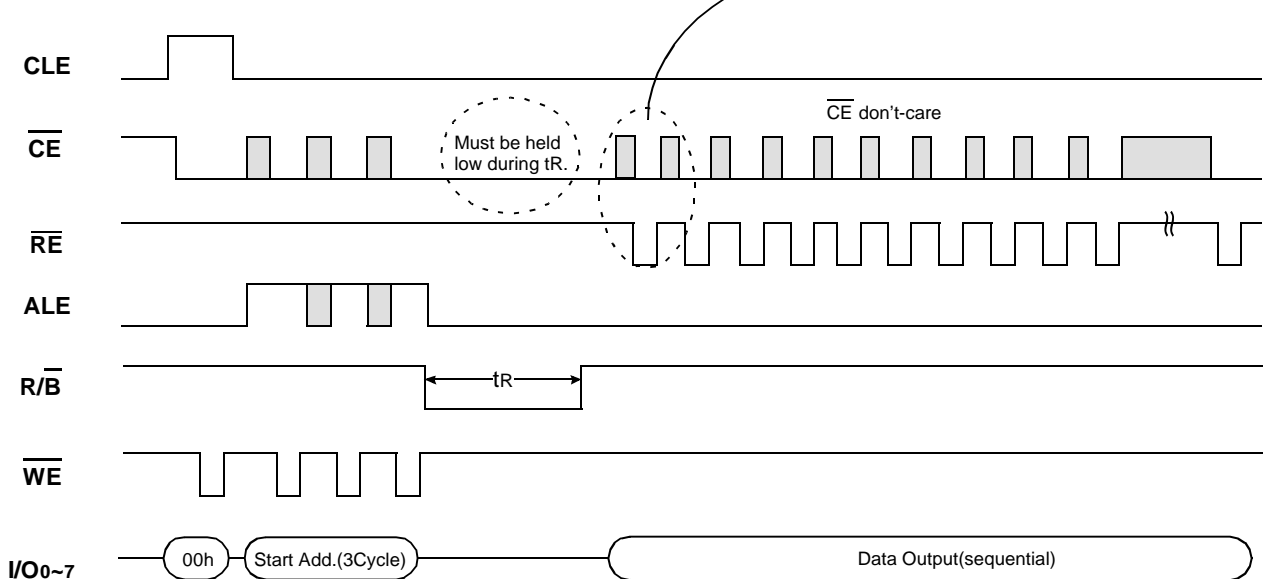
Figure 3. Program Operation with $\overline{\text{CE}}$ don't-care.



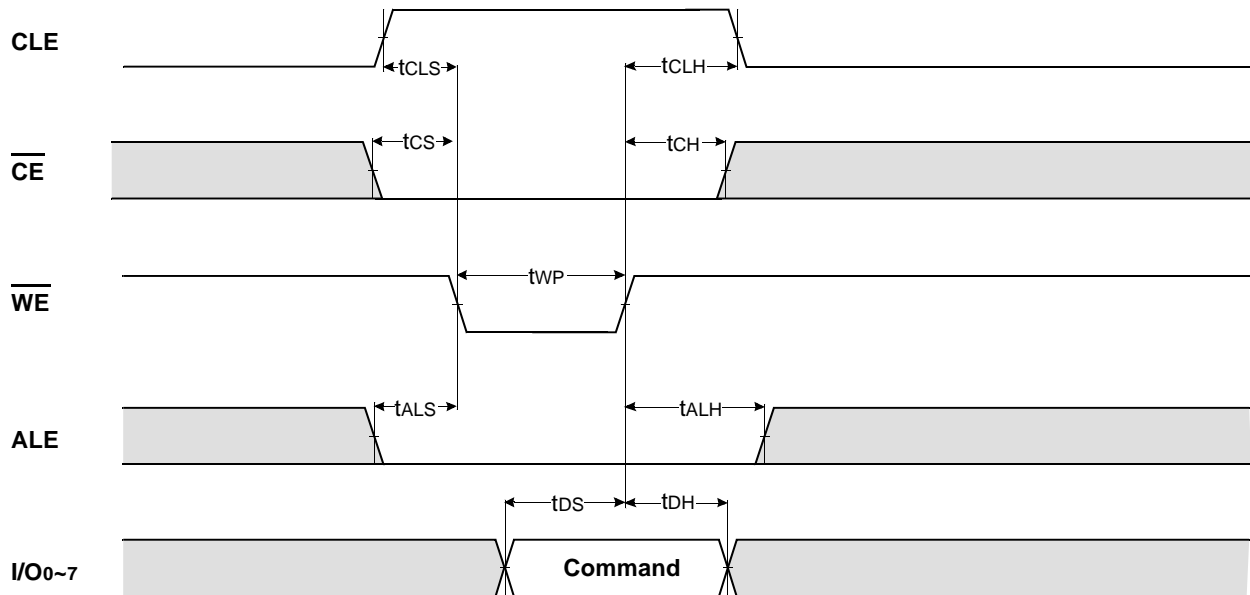
Timing requirements : If $\overline{\text{CE}}$ is exerted high during data-loading, tCS must be minimum 10ns and tWC must be increased accordingly.

Timing requirements : If $\overline{\text{CE}}$ is exerted high during sequential data-reading, the falling edge of $\overline{\text{CE}}$ to valid data(tCEA) must be kept greater than 45ns.

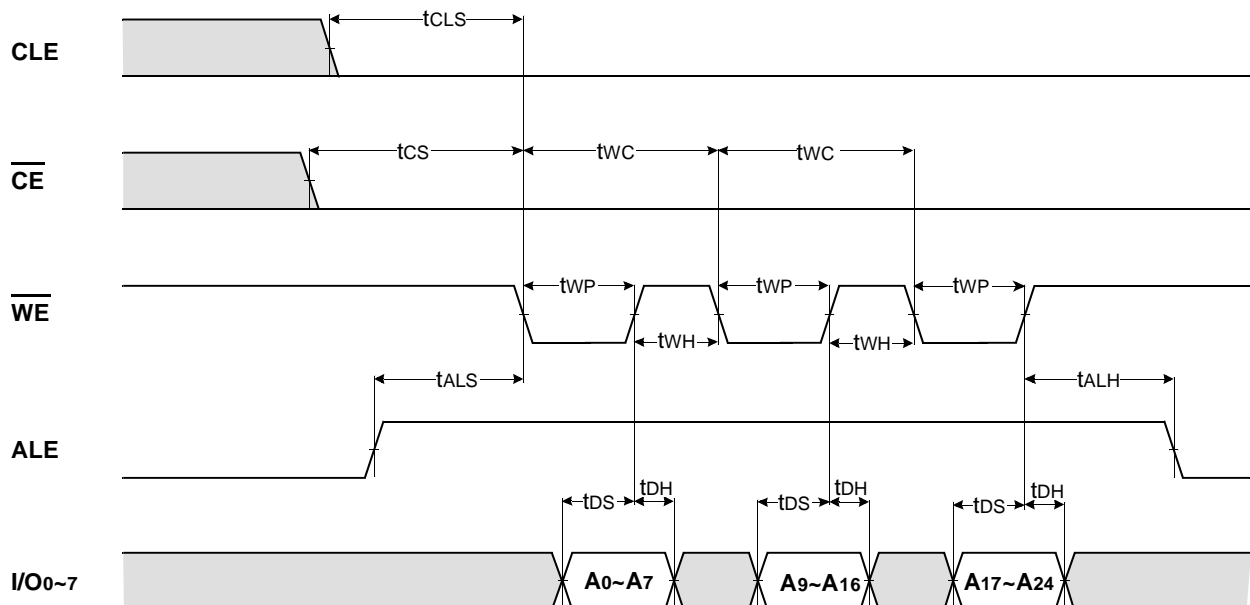
Figure 4. Read Operation with $\overline{\text{CE}}$ don't-care.



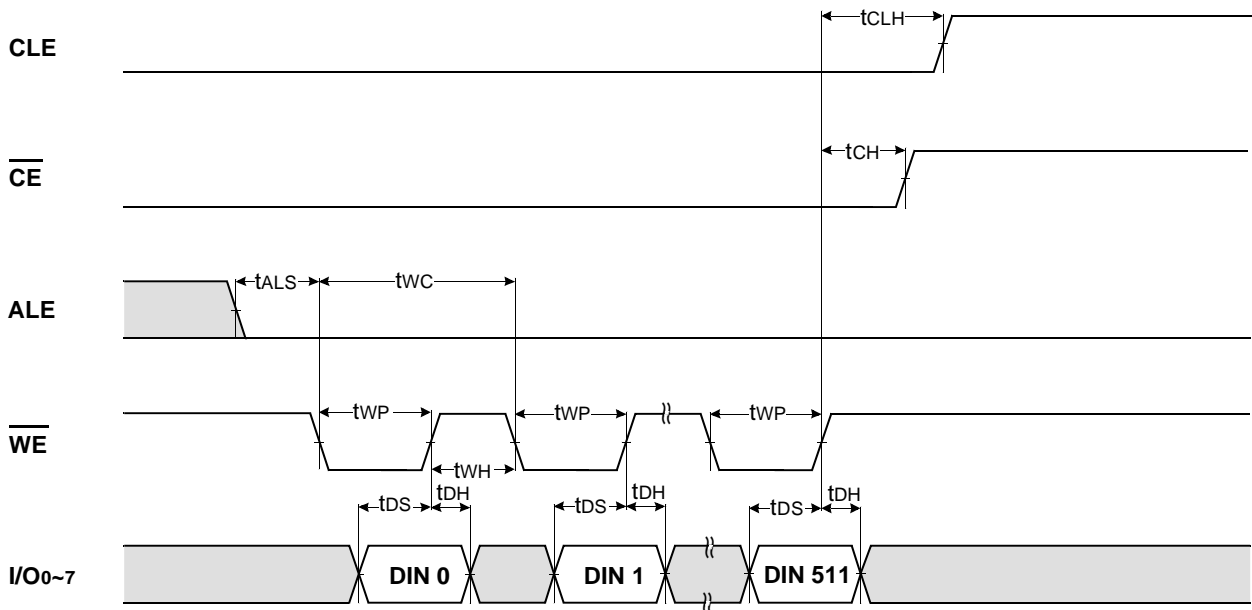
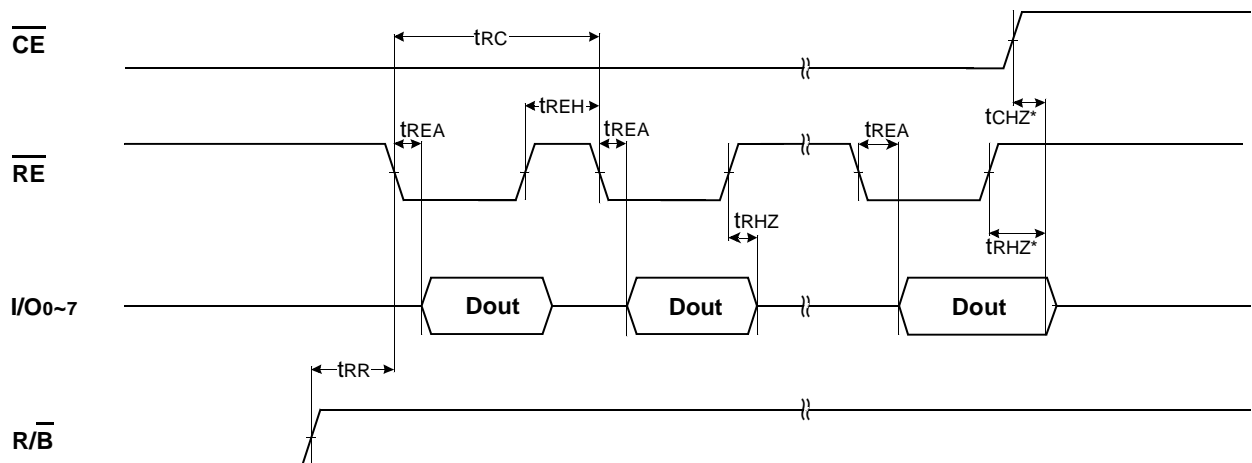
* Command Latch Cycle



* Address Latch Cycle



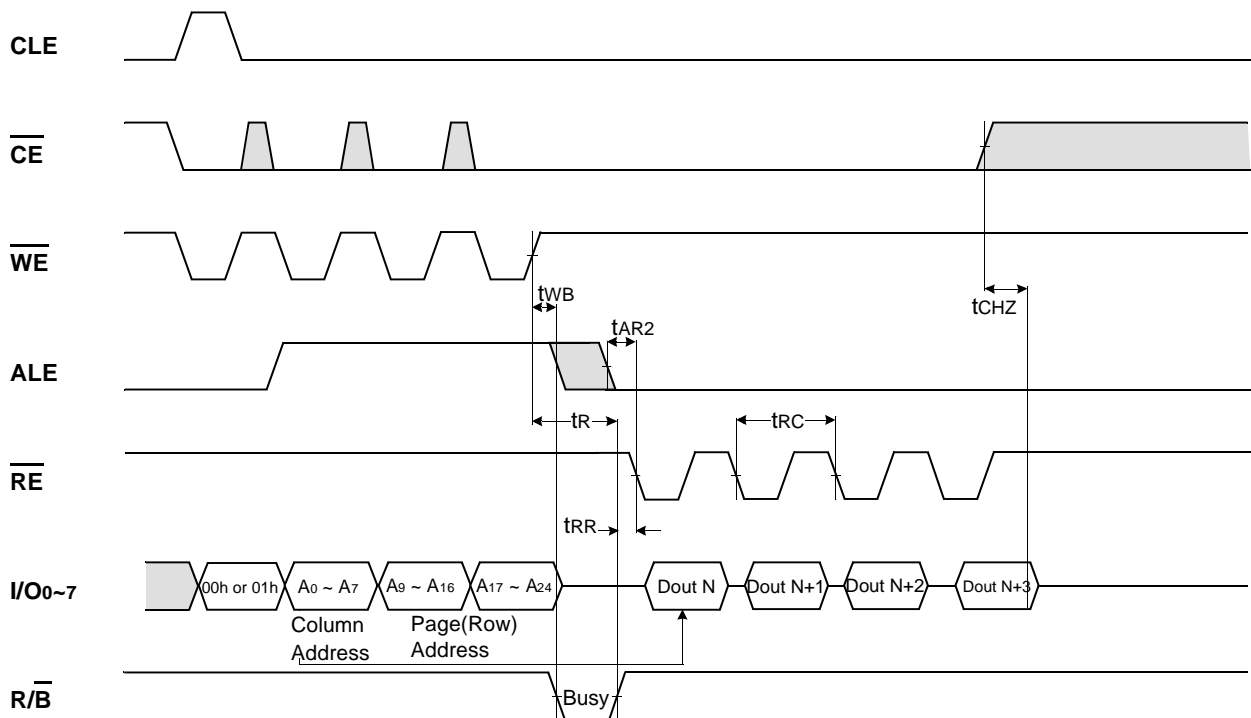
* Input Data Latch Cycle

* Sequential Out Cycle after Read (CLE=L, \overline{WE} =H, ALE=L)

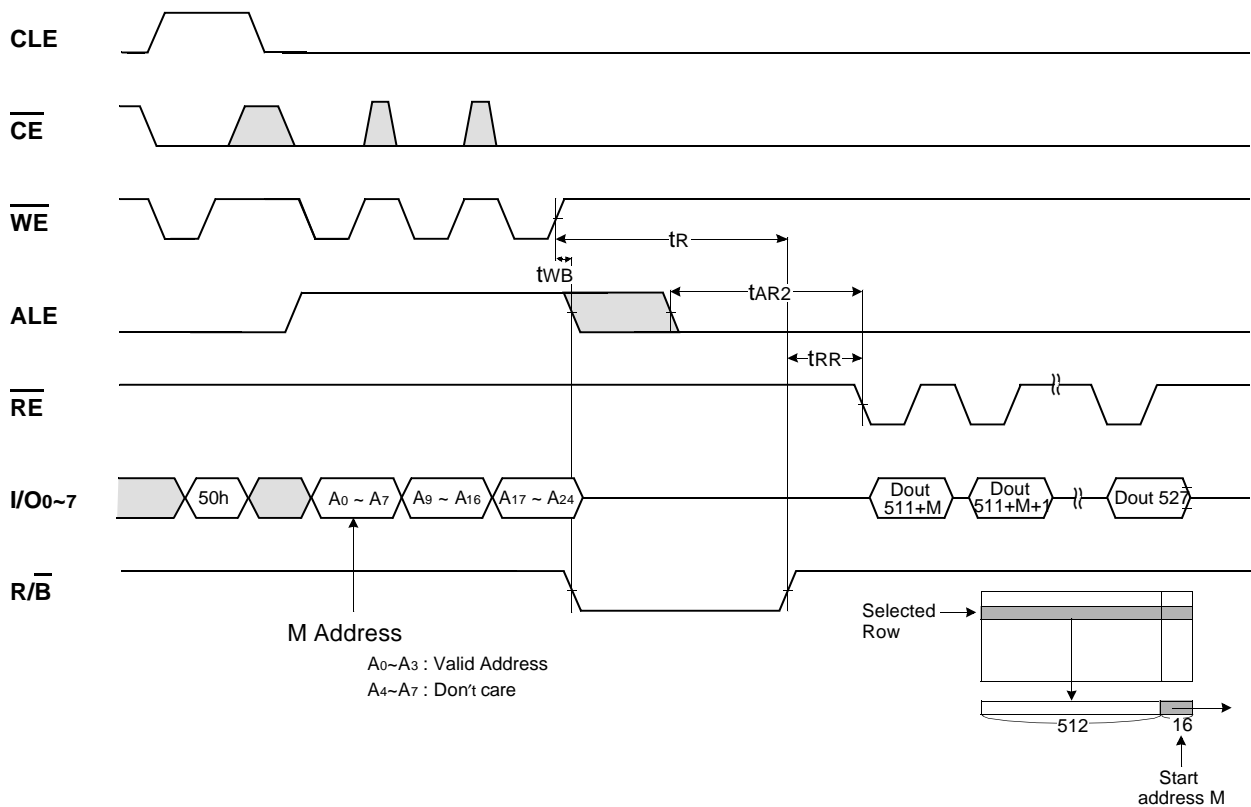
NOTES : Transition is measured $\pm 200\text{mV}$ from steady state voltage with load.
This parameter is sampled and not 100% tested.

The timing diagram illustrates the sequence of signals for a memory access cycle. The signals and their timing parameters are as follows:

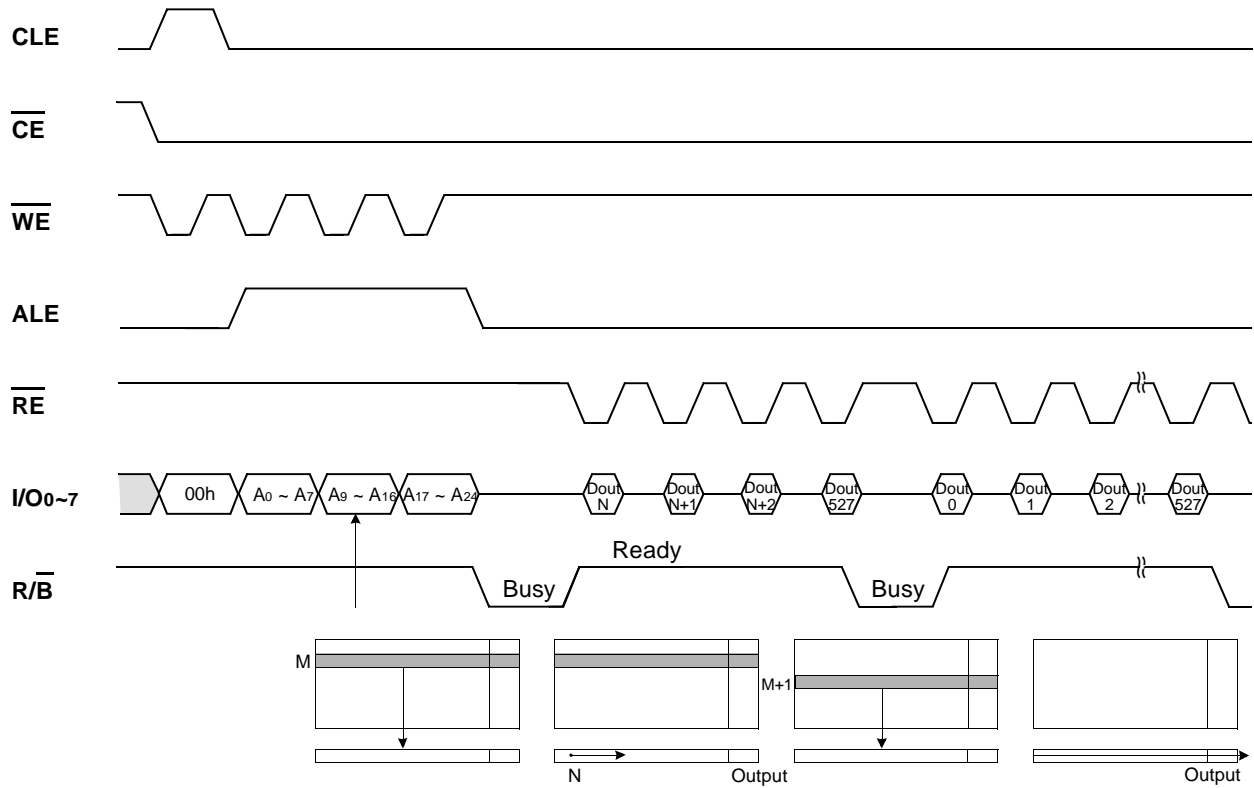
- CLE**: Chip Enable, active high. Timing parameter: t_{CEH} (high pulse width).
- CE**: Chip Enable, active low. Timing parameter: t_{CHZ} (high impedance time after falling edge).
- WE**: Write Enable, active low. Timing parameter: t_{WC} (write pulse width).
- ALE**: Address Latch Enable, active high. Timing parameters: t_{WB} (write buffer enable time), t_{AR2} (address latch time), and t_R (read time).
- RE**: Read Enable, active low. Timing parameters: t_{RC} (read time), t_{RR} (read refresh time), t_{RHZ} (high impedance time after falling edge), and t_{RB} (read buffer time).
- I/O0~7**: Data bus. The diagram shows the sequence of data: 00h or 01h, Column Address (A0 ~ A7), Page(Row) Address (A9 ~ A16, A17 ~ A24), and Data (Dout N, Dout N+1, ..., Dout 527).
- R/B**: Read/Write control signal, active low. Timing parameter: t_{RB} (read buffer time).

READ1 OPERATION (INTERCEPTED BY \overline{CE})

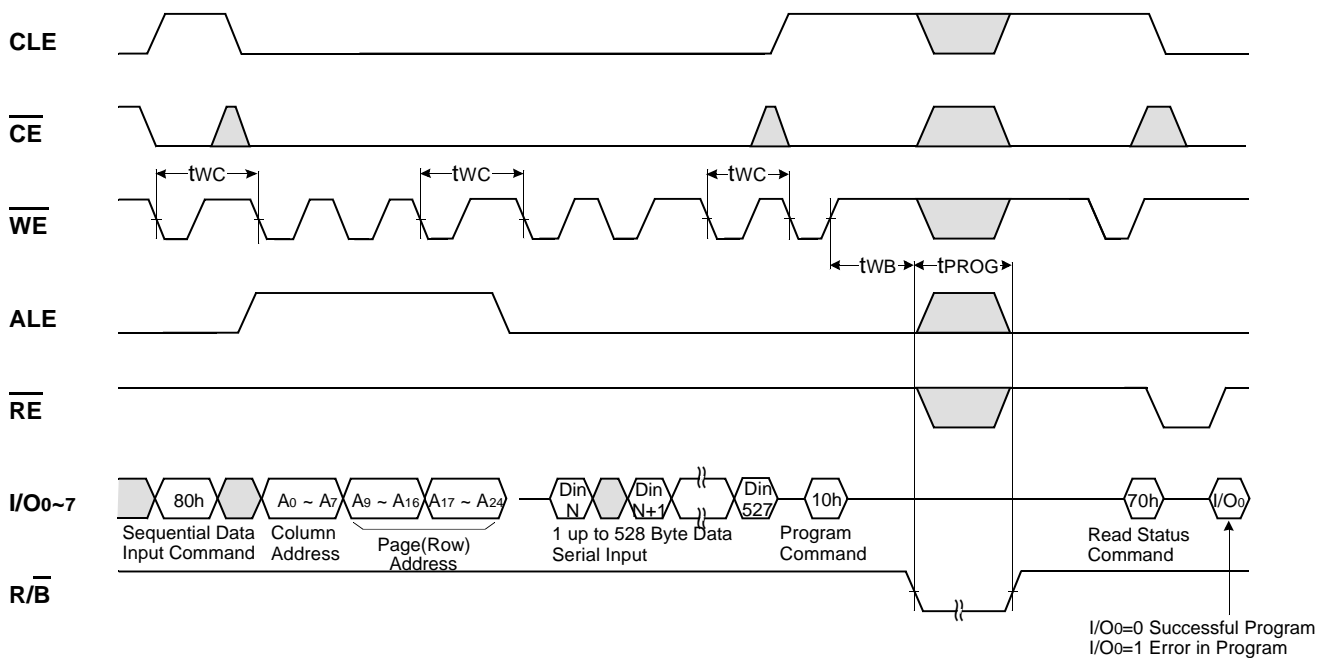
READ2 OPERATION (READ ONE PAGE)



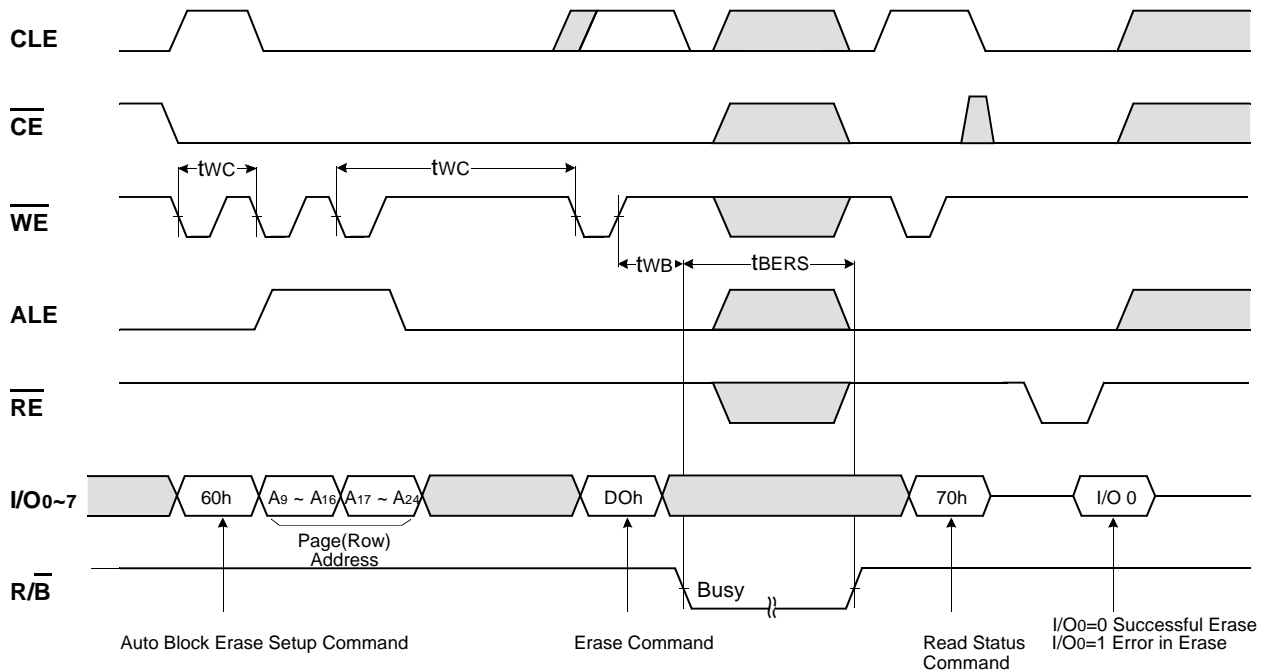
SEQUENTIAL ROW READ OPERATION (WITHIN A BLOCK)



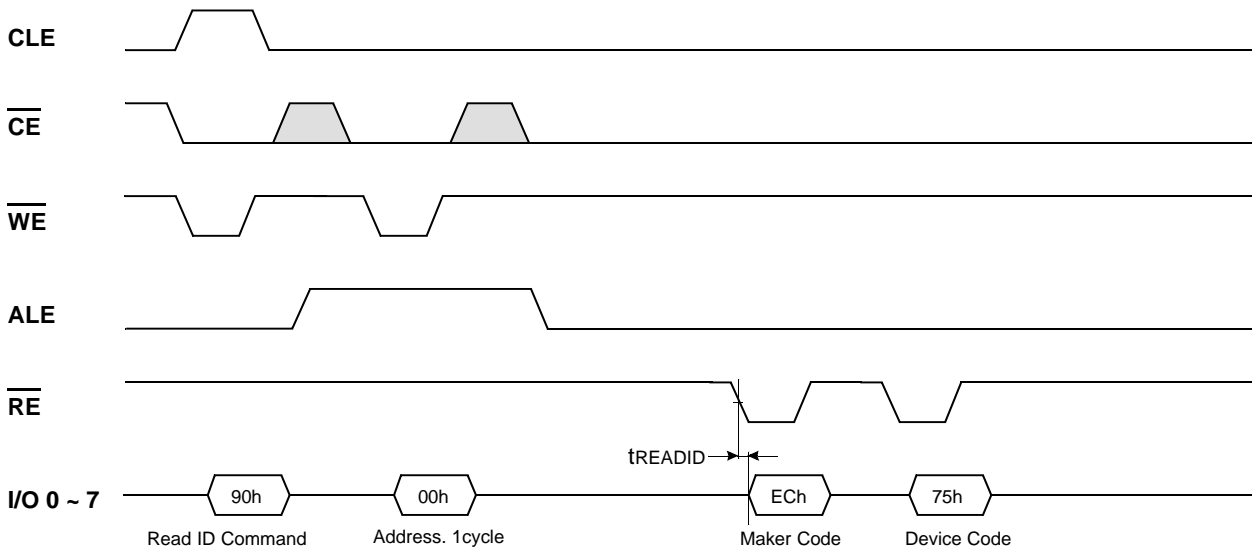
PAGE PROGRAM OPERATION



BLOCK ERASE OPERATION(ERASE ONE BLOCK)



MANUFACTURE & DEVICE ID READ OPERATION



DEVICE OPERATION

PAGE READ

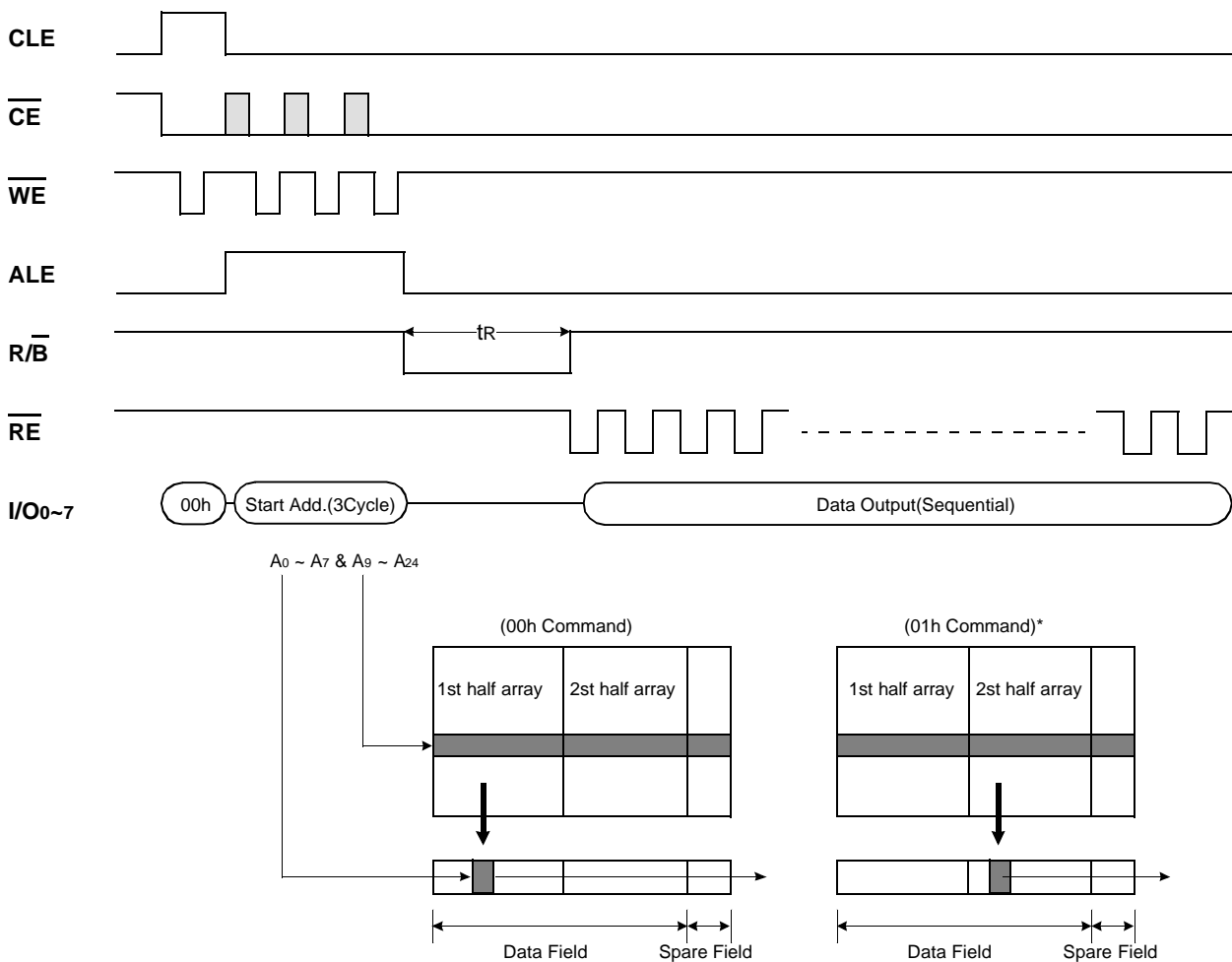
Upon initial device power up, the device defaults to Read1 mode. This operation is also initiated by writing 00h to the command register along with three address cycles. Once the command is latched, it does not need to be written for the following page read operation. Three types of operations are available : random read, serial page read and sequential row read.

The random read mode is enabled when the page address is changed. The 528 bytes of data within the selected page are transferred to the data registers in less than 10 μ s(t_R). The system controller can detect the completion of this data transfer(t_R) by analyzing the output of R/B pin. Once the data in a page is loaded into the registers, they may be read out in 50ns cycle time by sequentially pulsing RE. High to low transitions of the RE clock output the data starting from the selected column address up to the last column address.

After the data of last column address is clocked out, the next page is automatically selected for sequential row read.

Waiting 10 μ s again allows reading the selected page. The sequential row read operation is terminated by bringing \overline{CE} high. The way the Read1 and Read2 commands work is like a pointer set to either the main area or the spare area. The spare area of bytes 512 to 527 may be selectively accessed by writing the Read2 command. Addresses A₀ to A₃ set the starting address of the spare area while addresses A₄ to A₇ are ignored. Unless the operation is aborted, the page address is automatically incremented for sequential row read as in Read1 operation and spare sixteen bytes of each page may be sequentially read. The Read1 command(00h/01h) is needed to move the pointer back to the main area. Figures 3 thru 6 show typical sequence and timings for each read operation.

Figure 3. Read1 Operation



* After data access on 2nd half array by 01h command, the start pointer is automatically moved to 1st half array (00h) at next cycle.

Figure 4. Read2 Operation

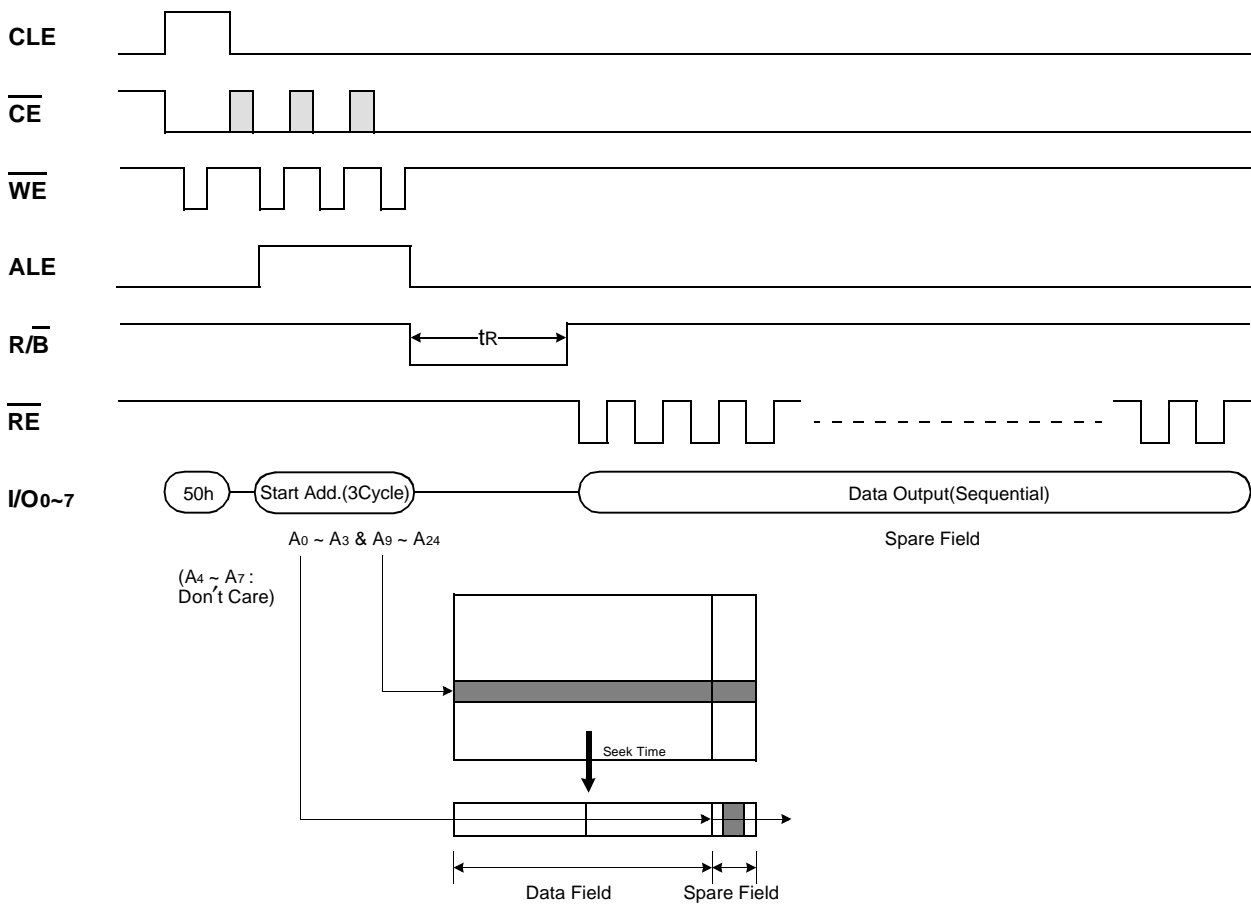
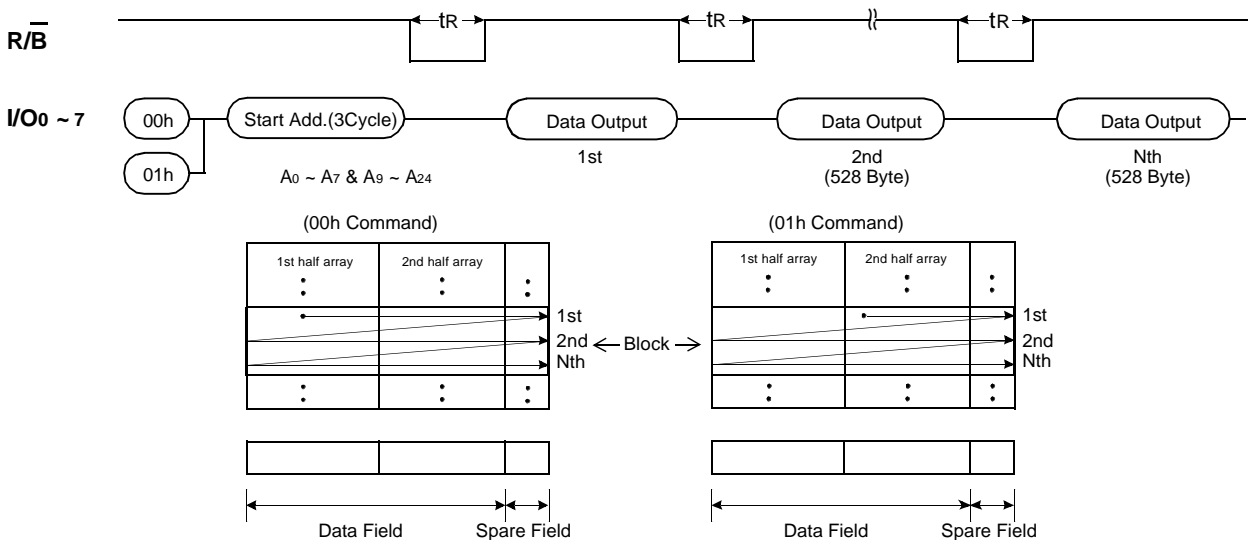
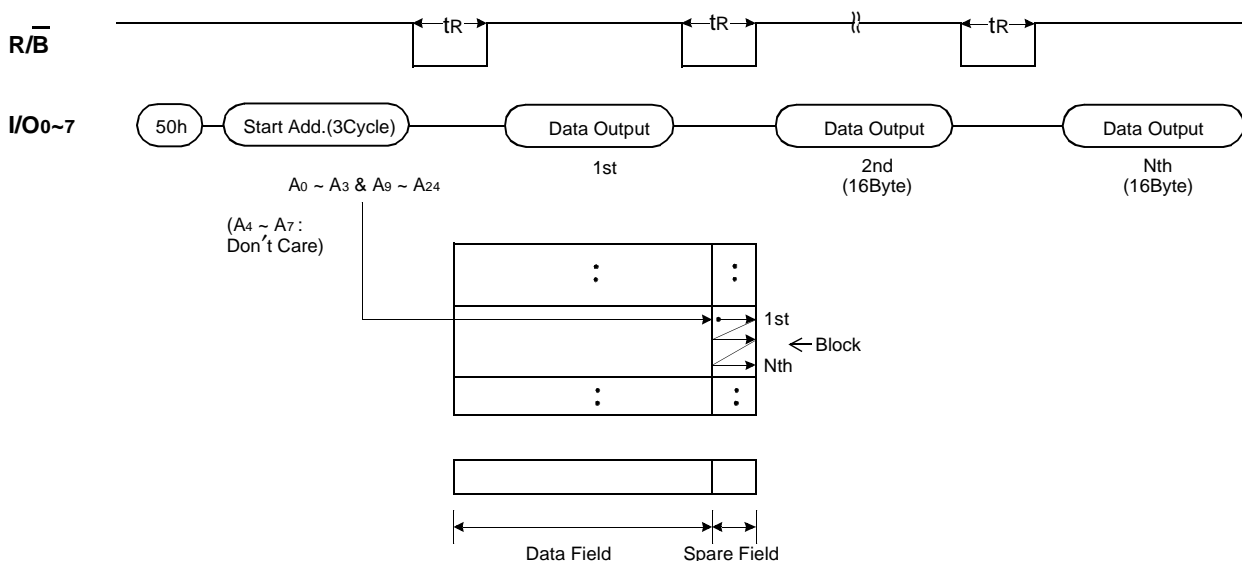


Figure 5. Sequential Row Read1 Operation



The Sequential Read 1 and 2 operation is allowed only within a block and after the last page of a block is read-out, the sequential read operation must be terminated by bringing \overline{CE} high. When the page address moves onto the next block, read command and address must be given.

Figure 6. Sequential Row Read2 Operation

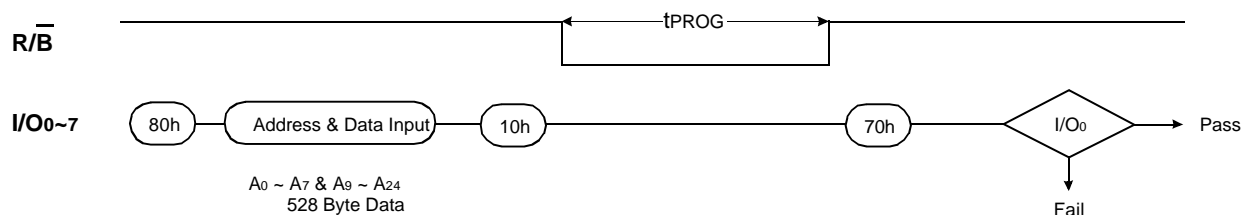


PAGE PROGRAM

The device is programmed basically on a page basis, but it does allow multiple partial page programming of a byte or consecutive bytes up to 528, in a single page program cycle. The number of consecutive partial page programming operation within the same page without an intervening erase operation must not exceed 2 for main array and 3 for spare array. The addressing may be done in any random order in a block. A page program cycle consists of a serial data loading period in which up to 528 bytes of data may be loaded into the page register, followed by a non-volatile programming period where the loaded data is programmed into the appropriate cell. Serial data loading can be started from 2nd half array by moving pointer. About the pointer operation, please refer to the attached technical notes.

In order to serial data loading period begins by inputting the Serial Data Input command(80h), followed by the three cycle address input and then serial data loading. The bytes other than those to be programmed do not need to be loaded. The Page Program confirm command(10h) initiates the programming process. Writing 10h alone without previously entering the serial data will not initiate the programming process. The internal write controller automatically executes the algorithms and timings necessary for program and verify, thereby freeing the system controller for other tasks. Once the program process starts, the Read Status Register command may be entered, with \overline{RE} and \overline{CE} low, to read the status register. The system controller can detect the completion of a program cycle by monitoring the $\overline{R/B}$ output, or the Status bit(I/O 6) of the Status Register. Only the Read Status command and Reset command are valid while programming is in progress. When the Page Program is complete, the Write Status Bit(I/O 0) may be checked(Figure 7). The internal write verify detects only errors for "1"s that are not successfully programmed to "0"s. The command register remains in Read Status command mode until another valid command is written to the command register.

Figure 7. Program & Read Status Operation



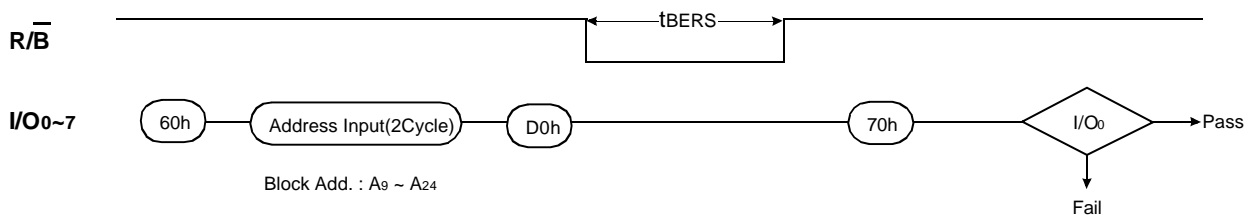
BLOCK ERASE

The Erase operation is done on a block(16K Byte) basis. Block address loading is accomplished in two cycles initiated by an Erase Setup command(60h). Only address A14 to A24 is valid while A9 to A13 is ignored. The Erase Confirm command(D0h) following the block address loading initiates the internal erasing process. This two-step sequence of setup followed by execution command ensures that memory contents are not accidentally erased due to external noise conditions.

At the rising edge of \overline{WE} after the erase confirm command input, the internal write controller handles erase, erase-verify and pulse repetition where required. When the erase operation is completed, the Write Status Bit(I/O 0) may be checked.

Figure 8 details the sequence.

Figure 8. Block Erase Operation



READ STATUS

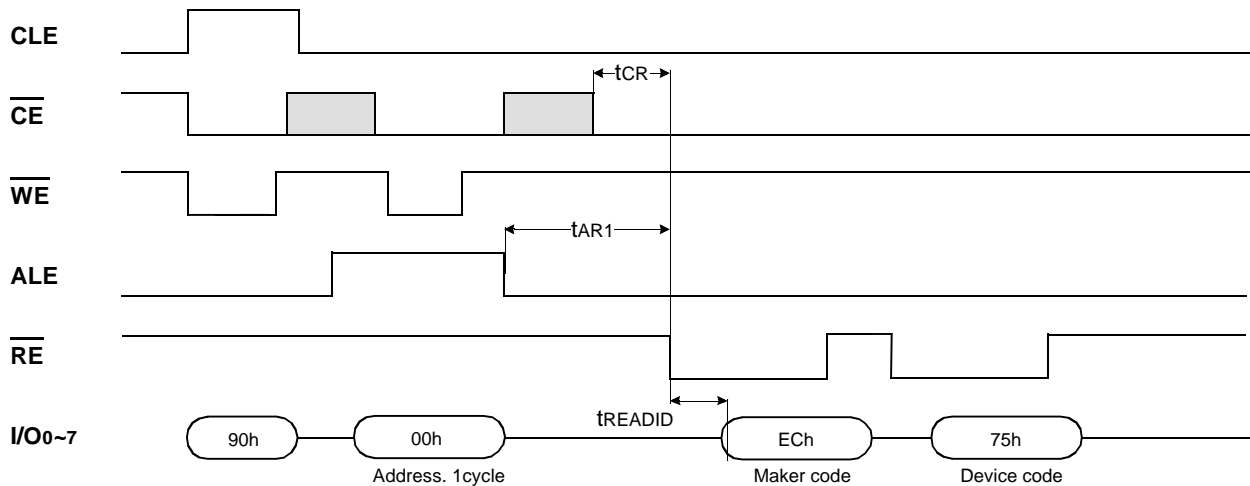
The device contains a Status Register which may be read to find out whether program or erase operation is completed, and whether the program or erase operation is completed successfully. After writing 70h command to the command register, a read cycle outputs the content of the Status Register to the I/O pins on the falling edge of \overline{CE} or \overline{RE} , whichever occurs last. This two line control allows the system to poll the progress of each device in multiple memory connections even when $\overline{R/B}$ pins are common-wired. \overline{RE} or \overline{CE} does not need to be toggled for updated status. Refer to table 2 for specific Status Register definitions. The Pass/Fail status on $I/O 0$ is only valid when the device is in the Ready state. The command register remains in Status Read mode until further commands are issued to it. Therefore, if the status register is read during a random read cycle, a read command(00h or 50h) should be given before sequential page read cycle.

Table2. Read Status Register Definition

I/O #	Status	Definition
I/O 0	Program / Erase	"0" : Successful Program / Erase "1" : Error in Program / Erase
I/O 1	Reserved for Future Use	"0"
I/O 2		"0"
I/O 3		"0"
I/O 4		"0"
I/O 5		"0"
I/O 6	Device Operation	"0" : Busy "1" : Ready
I/O 7	Write Protect	"0" : Protected "1" : Not Protected

READ ID

The device contains a product identification mode, initiated by writing 90h to the command register, followed by an address input of 00h. Two read cycles sequentially output the manufacture code (ECh), and the device code (75h) respectively. The command register remains in Read ID mode until further commands are issued to it. Figure 9 shows the operation sequence.

Figure 9. Read ID Operation**RESET**

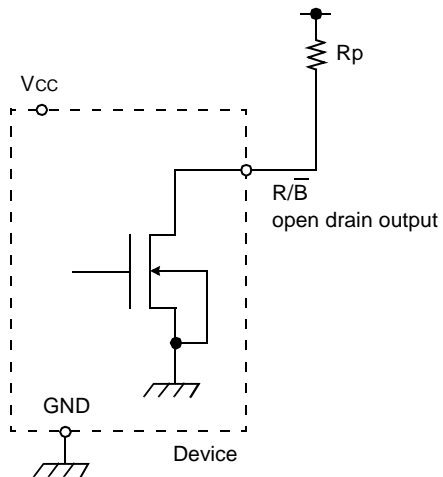
The device offers a reset feature, executed by writing FFh to the command register. When the device is in Busy state during random read, program or erase mode, the reset operation will abort these operations. The contents of memory cells being altered are no longer valid, as the data will be partially programmed or erased. The command register is cleared to wait for the next command, and the Status Register is cleared to value C0h when WP is high. Refer to table 3 for device status after reset operation. If the device is already in reset state a new reset command will not be accepted by the command register. The R/B pin transitions to low for tRST after the Reset command is written. Reset command is not necessary for normal operation. Refer to Figure 10 below.

Figure 10. RESET Operation**Table3. Device Status**

	After Power-up	After Reset
Operation Mode	Read 1	Waiting for next command

READY/BUSY

The device has a $\overline{R/B}$ output that provides a hardware method of indicating the completion of a page program, erase and random read completion. The $\overline{R/B}$ pin is normally high but transitions to low after program or erase command is written to the command register or random read is started after address loading. It returns to high when the internal controller has finished the operation. The pin is an open-drain driver thereby allowing two or more $\overline{R/B}$ outputs to be Or-tied. An appropriate pull-up resistor is required for proper operation and the value may be calculated by the following equation.



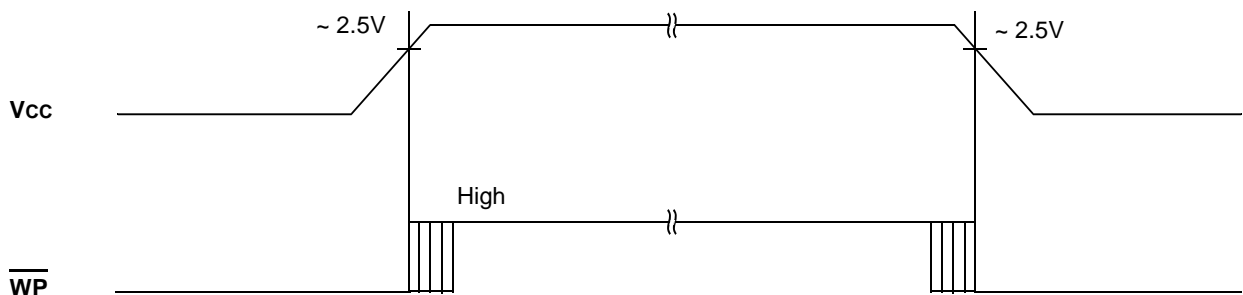
$$R_p = \frac{V_{CC}(\text{Max.}) - V_{OL}(\text{Max.})}{I_{OL} + \Sigma I_L} = \frac{3.2V}{8mA + \Sigma I_L}$$

where I_L is the sum of the input currents of all devices tied to the $\overline{R/B}$ pin.

DATA PROTECTION

The device is designed to offer protection from any involuntary program/erase during power-transitions. An internal voltage detector disables all functions whenever V_{CC} is below about 2V. \overline{WP} pin provides hardware protection and is recommended to be kept at V_{IL} during power-up and power-down as shown in Figure 11. The two step command sequence for program/erase provides additional software protection.

Figure 11. AC Waveforms for Power Transition



DIMENSIONS

Unit:mm

22 PAD SOLID STATE FLOPPY DISK CARD (3.3V)

SOLID STATE PRODUCT OUTLINE

